1-Channel ESD Protector

Product Description

The HBL1010 provides robust ESD protection for sensitive parts that may be subjected to electrostatic discharge (ESD). The tiny form factor means it can be used in very confined spaces. The electrical 'back-to-back Zener' configuration provides symmetrical ESD protection in cases where nodes with AC signals are present. This device is designed and characterized to safely dissipate ESD strikes of at least ± 8 kV, according to the MIL-STD-883 (Method 3015) specification for Human Body Model (HBM) ESD.

Features

- Compact Die Protects from ESD Discharges
- Almost no Conduction at Signal Amplitudes less than ±4 V
- ESD Protection to over ±8 kV Contact Discharge per MIL_STD_883 International ESD Standard
- These Devices are Pb-Free and are RoHS Compliant

Applications

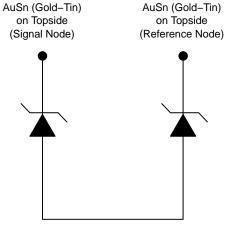
- LED Lighting
- Modules
- Interface Circuits



ON Semiconductor®

www.onsemi.com

ELECTRICAL SCHEMATIC



Silicon Substrate on Backside

Table 1. ORDERING INFORMATION[†]

Part Numbering Information						
Ordering Part Number	Topside Metal	Back Metal	BG Thickness	Inking?	Shipping Method	
HBL1010RP	Gold–Tin (AuSn)	None (Si Substrate)	4 mils	No	Die on tape in ring-pack	

NOTE: Contact your sales representative for other ordering options.

HBL1010

SPECIFICATIONS

Table 2. OPERATING CONDITIONS

Parameter	Rating	Units	
Operating Temperature Range	-40 to +130	°C	
Storage Temperature Range	-55 to +130	°C	

Table 3. ELECTRICAL OPERATING CHARACTERISTICS

Symbol	Parameter	Conditions	Min	Тур	Max	Units
I _{LEAK}	Leakage Current	V = ±4 V, T = 25°C		±0.1	±1	μΑ
		V = ±7 V, T = 25°C		±10	±100	μΑ
V _{BD}	Breakdown Voltage	T = 25°C at ±20.0 mA	±7.3	±8	±8.9	V
V _{ESD}	ESD Voltage Rating Contact Discharge per Human Body Model, MIL–STD–883 (Method 3015)	T = 25°C (Note 1)	±8			kV
CT	Capacitance	T = 25°C		18		pF
	Temp Coefficient of BV	20 mA		1.0		mV/K

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

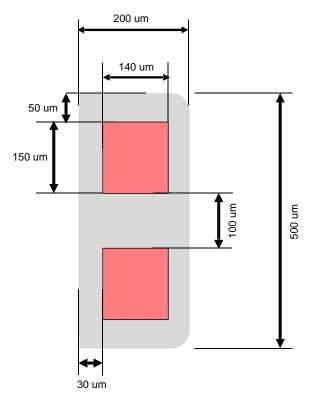
1. Per the standard, 3 positive and 3 negative strikes are applied, one second apart.

MECHANICAL DETAILS

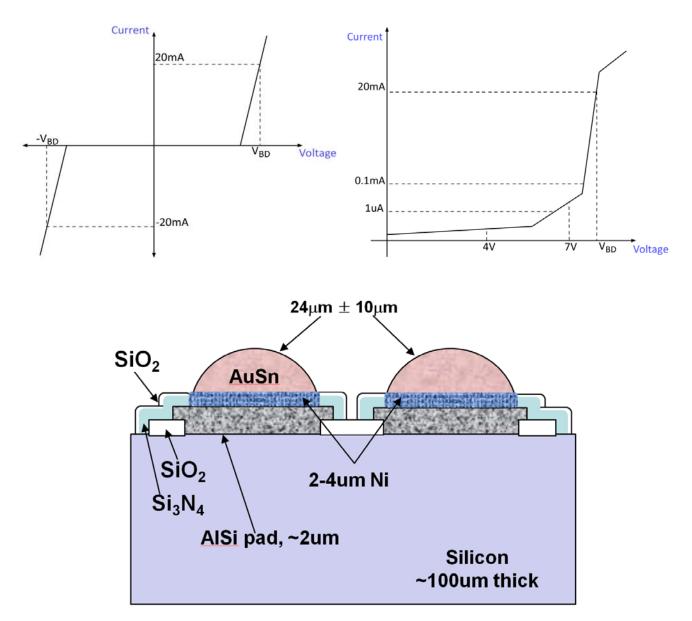
Table 4. MECHANICAL SPECIFICATIONS (Note 2)

Symbol	Value	Unit
Composition	Silicon Wafer, P+ doped	
Length (Sawn)	500	μm
Width (Sawn)	200	μm
Thickness	4	mils
Top Pad Length	150	μm
Top Pad Width	140	μm
Top Pad Spacing	100	μm
Top Pad Composition	AuSn (gold–tin)	
Top Pad Thickness	24 ± 10	μm
Back Metal (Underside)	None (silicon substrate)	

2. Dimensions are typical values if tolerances are not specified.



HBL1010



ON Semiconductor and the intervent and the intervent of the pattern of the patter

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor P.O. Box 5163, Denver, Colorado 80217 USA Phone: 303–675–2175 or 800–344–3860 Toll Free USA/Canada Fax: 303–675–2176 or 800–344–3867 Toll Free USA/Canada Email: orderlit@onsemi.com N. American Technical Support: 800–282–9855 Toll Free USA/Canada Europe, Middle East and Africa Technical Support:

Phone: 421 33 790 2910 Japan Customer Focus Center Phone: 81–3–5817–1050 ON Semiconductor Website: www.onsemi.com

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative